SEMiX305TMLI17E4CV1

SEMiX® 5

3-Level TNPC IGBT-Module

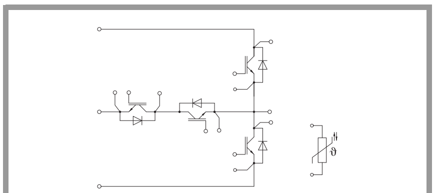
SEMiX305TMLI17E4CV1

Features*

- Solderless assembling solution with PressFIT signal pins and screw power terminals
- IGBT 4 Trench Gate Technology
- $V_{CE(sat)}$ with positive temperature coefficient
- Low inductance case
- Reliable mechanical design with injection moulded terminals and reliable internal connections
- UL recognized file no. E63532
- NTC temperature sensor inside

Remarks*

- Case temperature limited to T_C=125°C max.
- Product reliability results are valid for T_{jop}=150°C
- IGBT1: outer IGBTs T1 & T4
- IGBT2: inner IGBTs T2 & T3
- Diode1: outer diodes D1 & D4
- Diode2: inner diodes D2 & D3
- Dynamic data are estimated
- For storage and case temperature with TIM see document “ TP (HALA P8) SEMiX5p “



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Absolute Maximum Ratings

Symbol	Conditions		Values	Unit
IGBT1				
V_{CES}			1700	V
I_C	T_j = 175 °C	T_c = 25 °C	486	A
		T_c = 80 °C	376	A
I_{Cnom}			300	A
I_{CRM}			600	A
V_{GES}			-20 ... 20	V
t_{psc}	V_{CC} = 1000 V, V_{GE} ≤ 15 V, T_j = 150 °C, V_{CES} ≤ 1700 V		10	µs
T_j			-40 ... 175	°C
IGBT2				
V_{CES}			1200	V
I_C	T_j = 175 °C	T_c = 25 °C	408	A
		T_c = 80 °C	313	A
I_{Cnom}			300	A
I_{CRM}			600	A
V_{GES}			-20 ... 20	V
t_{psc}	V_{CC} = 800 V, V_{GE} ≤ 15 V, T_j = 150 °C, V_{CES} ≤ 1200 V		10	µs
T_j			-40 ... 175	°C
Diode1				
V_{RRM}	T_j = 25 °C		1700	V
I_F	T_j = 175 °C	T_c = 25 °C	338	A
		T_c = 80 °C	250	A
I_{FRM}			600	A
I_{FSM}	10 ms, sin 180°, T_j = 25 °C		1836	A
T_j			-40 ... 175	°C
Diode2				
V_{RRM}	T_j = 25 °C		1200	V
I_F	T_j = 175 °C	T_c = 25 °C	312	A
		T_c = 80 °C	232	A
I_{FRM}			600	A
I_{FSM}	10 ms, sin 180°, T_j = 25 °C		1620	A
T_j			-40 ... 175	°C
Module				
$I_{t(RMS)}$			400	A
T_{stg}	module without TIM		-40 ... 125	°C
V_{isol}	AC sinus 50Hz, t = 1 min		4000	V

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Typical Applications

- UPS
- Solar
- Motor drives

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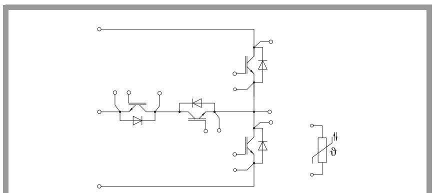

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Characteristics

Symbol	Conditions		min.	typ.	max.	Unit
IGBT1						
$V_{CE(sat)}$	I_C = 300 A, V_{GE} = 15 V, chiplevel	T_j = 25 °C		1.90	2.20	V
		T_j = 150 °C		2.30	2.60	V
V_{CE0}	chiplevel	T_j = 25 °C		0.80	0.90	V
		T_j = 150 °C		0.70	0.80	V
r_{CE}	V_{GE} = 15 V, chiplevel	T_j = 25 °C		3.7	4.3	mΩ
		T_j = 150 °C		5.3	6.0	mΩ
$V_{GE(th)}$	V_{GE} = V_{CE}, I_C = 12 mA		5.2	5.8	6.4	V
I_{CES}	V_{GE} = 0 V, V_{CE} = 1700 V, T_j = 25 °C				4.0	mA
C_{ies}	V_{CE} = 25 V, V_{GE} = 0 V	f = 1 MHz		27.2		nF
C_{oes}		f = 1 MHz		1.06		nF
C_{res}		f = 1 MHz		0.88		nF
Q_G	V_{GE} = - 8V...+15V			2400		nC
R_{Gint}	T_j = 25 °C			2.1		Ω
$t_{d(on)}$	V_{CC} = 1200 V, I_C = 300 A, V_{GE} = +15/-15 V, $R_{G\,on}$ = 1 Ω, $R_{G\,off}$ = 1 Ω, di/dt_{on} = 3765 A/µs, di/dt_{off} = 1725 A/µs, dv/dt = 3962 V/µs	T_j = 150 °C		135		ns
t_r		T_j = 150 °C		73		ns
E_{on}		T_j = 150 °C		38		mJ
$t_{d(off)}$		T_j = 150 °C		583		ns
t_f		T_j = 150 °C		139		ns
E_{off}		T_j = 150 °C		60		mJ
$R_{th(j-c)}$	per IGBT				0.08	K/W
$R_{th(c-s)}$	per IGBT (λgrease=0.81 W/(m*K))			0.03		K/W
$R_{th(c-s)}$	per IGBT, pre-applied phase change material			0.02		K/W
IGBT2						
$V_{CE(sat)}$	I_C = 300 A, V_{GE} = 15 V, chiplevel	T_j = 25 °C		1.80	2.05	V
		T_j = 150 °C		2.20	2.40	V
V_{CE0}	chiplevel	T_j = 25 °C		0.80	0.90	V
		T_j = 150 °C		0.70	0.80	V
r_{CE}	V_{GE} = 15 V, chiplevel	T_j = 25 °C		3.3	3.8	mΩ
		T_j = 150 °C		5.0	5.3	mΩ
$V_{GE(th)}$	V_{GE} = V_{CE}, I_C = 12 mA		5	5.8	6.5	V
I_{CES}	V_{GE} = 0 V, V_{CE} = 1200 V, T_j = 25 °C				4.0	mA
C_{ies}	V_{CE} = 25 V, V_{GE} = 0 V	f = 1 MHz		18.6		nF
C_{oes}		f = 1 MHz		1.16		nF
C_{res}		f = 1 MHz		1.02		nF
Q_G	V_{GE} = - 8V...+15V			1700		nC
R_{Gint}	T_j = 25 °C			2.5		Ω
$t_{d(on)}$	V_{CC} = 1200 V, I_C = 300 A, V_{GE} = +15/-8 V, $R_{G\,on}$ = 1 Ω, $R_{G\,off}$ = 1 Ω, di/dt_{on} = 3415 A/µs, di/dt_{off} = 2153 A/µs, dv/dt = 5133 V/µs	T_j = 150 °C		94		ns
t_r		T_j = 150 °C		75		ns
E_{on}		T_j = 150 °C		42		mJ
$t_{d(off)}$		T_j = 150 °C		481		ns
t_f		T_j = 150 °C		124		ns
E_{off}		T_j = 150 °C		35		mJ
$R_{th(j-c)}$	per IGBT				0.12	K/W
$R_{th(c-s)}$	per IGBT (λgrease=0.81 W/(m*K))			0.048		K/W
$R_{th(c-s)}$	per IGBT, pre-applied phase change material			0.023		K/W

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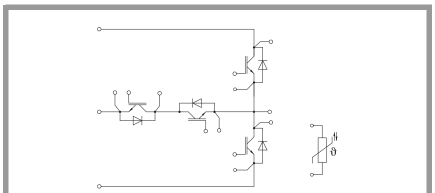

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Characteristics

Symbol	Conditions		min.	typ.	max.	Unit
Diode1						
$V_F = V_{EC}$	I_F = 300 A, V_{GE} = 0 V, chiplevel	T_j = 25 °C		2.00	2.40	V
		T_j = 150 °C		2.14	2.56	V
V_{F0}	chiplevel	T_j = 25 °C		1.32	1.56	V
		T_j = 150 °C		1.08	1.22	V
r_F	chiplevel	T_j = 25 °C		2.3	2.8	mΩ
		T_j = 150 °C		3.5	4.5	mΩ
I_{RRM}	I_F = 300 A, di/dt_{off} = 3415 A/µs, V_{CC} = 1200 V, V_{GE} = +15/-15 V	T_j = 150 °C		216.2		A
Q_{rr}		T_j = 150 °C		88.7		µC
E_{rr}		T_j = 150 °C		38		mJ
$R_{th(j-c)}$	per diode				0.17	K/W
$R_{th(c-s)}$	per diode (λgrease=0.81 W/(m*K))			0.04		K/W
$R_{th(c-s)}$	per diode, pre-applied phase change material			0.035		K/W
Diode2						
$V_F = V_{EC}$	I_F = 300 A, V_{GE} = 0 V, chiplevel	T_j = 25 °C		2.14	2.46	V
		T_j = 150 °C		2.07	2.38	V
V_{F0}	chiplevel	T_j = 25 °C		1.30	1.50	V
		T_j = 150 °C		0.90	1.10	V
r_F	chiplevel	T_j = 25 °C		2.8	3.2	mΩ
		T_j = 150 °C		3.9	4.3	mΩ
I_{RRM}	I_F = 300 A, di/dt_{off} = 3765 A/µs, V_R = 1200 V, V_{GE} = +15/-8 V	T_j = 150 °C		194.6		A
Q_{rr}		T_j = 150 °C		37.8		µC
E_{rr}		T_j = 150 °C		13		mJ
$R_{th(j-c)}$	per diode				0.21	K/W
$R_{th(c-s)}$	per diode (λgrease=0.81 W/(m*K))			0.058		K/W
$R_{th(c-s)}$	per diode, pre-applied phase change material			0.043		K/W
Module						
L_{sCE1}				31		nH
L_{CE}				42		nH
$R_{CC'+EE'}$	measured between terminal 5 and 1	T_C = 25 °C		0.8		mΩ
		T_C = 125 °C		1.1		mΩ
$Rth_{(c-s)1}$	calculated without thermal coupling			0.005		K/W
$Rth_{(c-s)2}$	including thermal coupling, T_s underneath module, P12 (reference)			0.009		K/W
$Rth_{(c-s)2}$	including thermal coupling, T_s underneath module, pre-applied phase change material			0.006		K/W
M_s	to heat sink (M5)		3		6	Nm
M_t		to terminals (M6)	3		6	Nm
						Nm
w				398		g
Temperature Sensor						
R_{100}	T_c=100°C (R_{25}=5 kΩ)			493 ± 5%		Ω
$B_{100/125}$	$R_{(T)}=R_{100}exp[B_{100/125}(1/T-1/T_{100})]$; T[K];			3550 ±2%		K

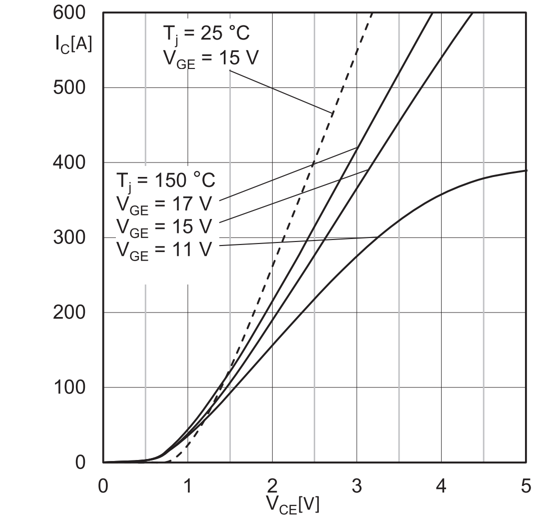


Fig. 1: Typ. output characteristic, inclusive $R_{CC'+EE'}$

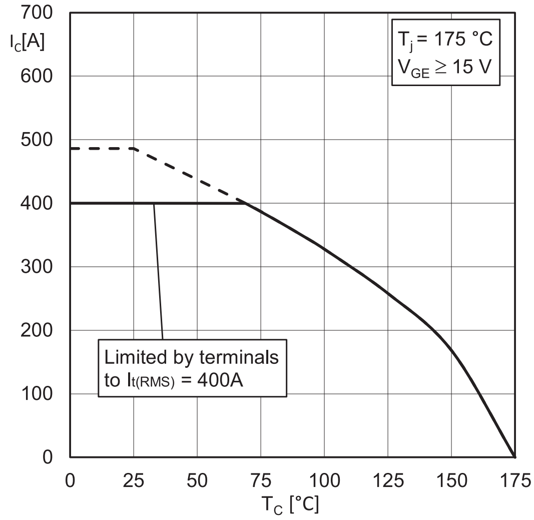


Fig. 2: IGBT1 rated current vs. Temperature I_c=f(T_c)

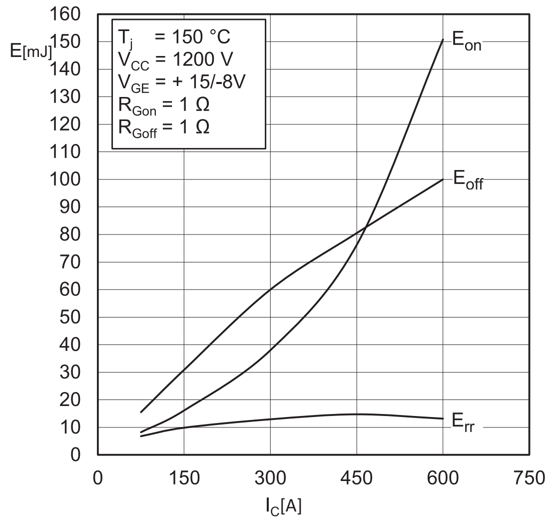


Fig. 3: Typ. IGBT1 & Diode2 turn-on /-off energy = f (I_C)

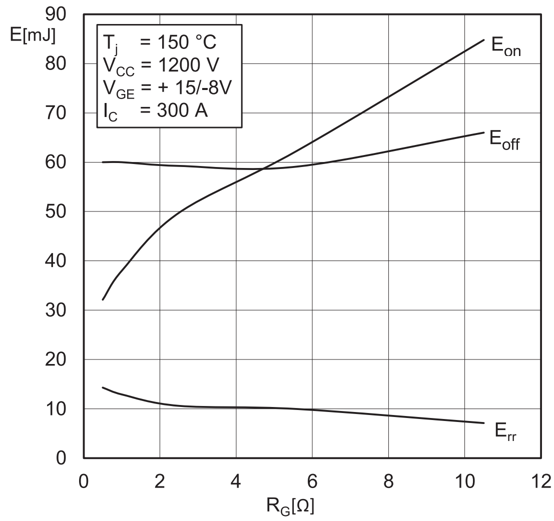


Fig. 4: Typ. IGBT1 & Diode2 turn-on /-off energy = f(R_G)

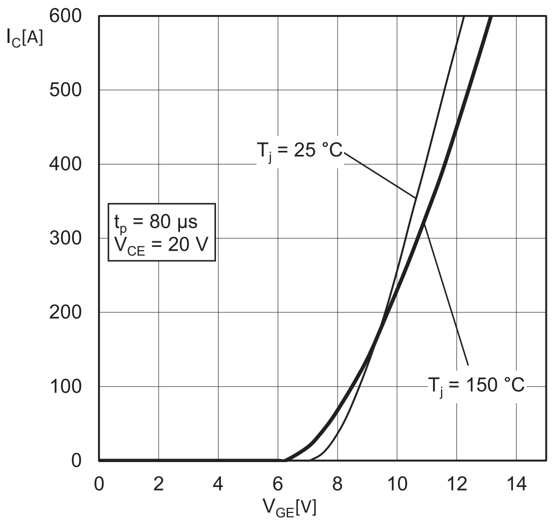


Fig. 5: Typ. IGBT1 transfer characteristic

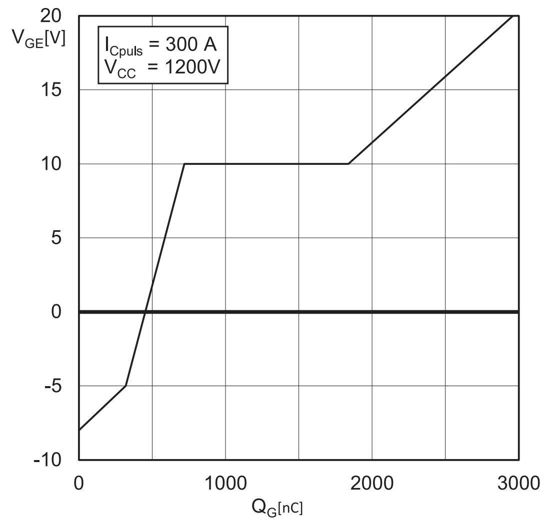


Fig. 6: Typ. IGBT1 gate charge characteristic

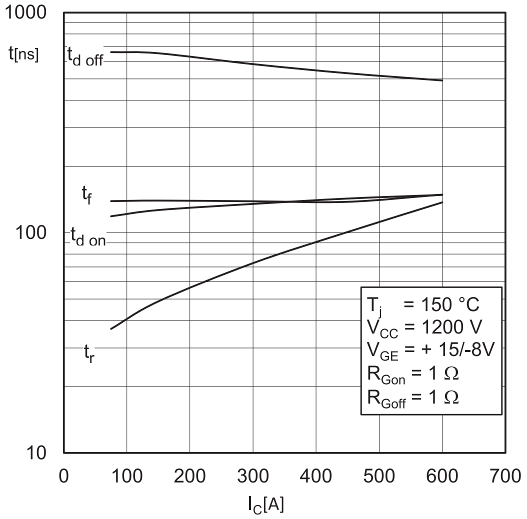


Fig. 7: Typ. IGBT2 switching times vs. I_C

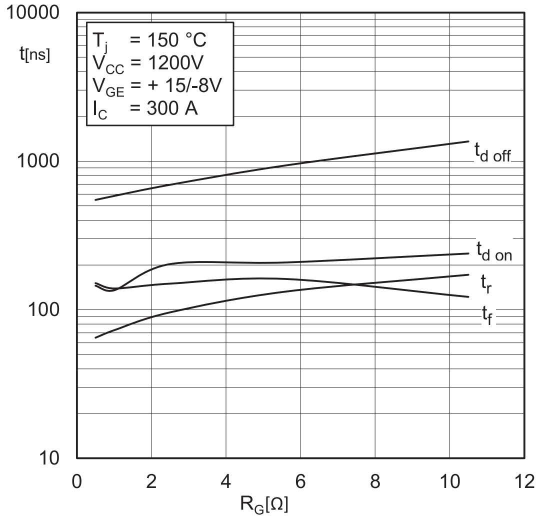


Fig. 8: Typ. switching times vs. gate resistor R_G

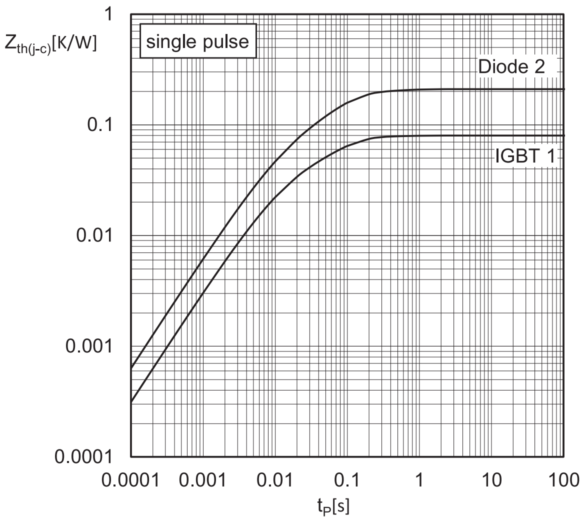


Fig. 9: Transient thermal impedance

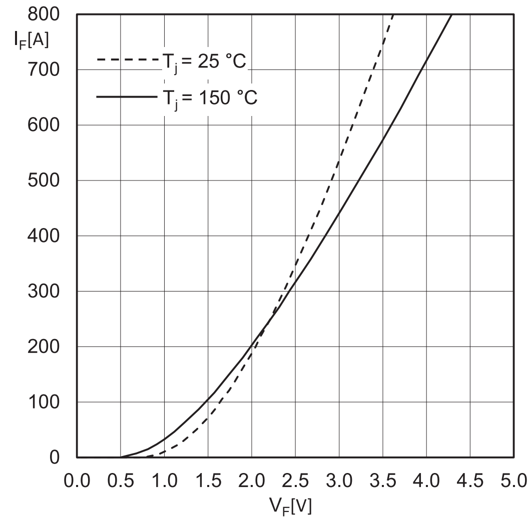


Fig. 10: Typ. CAL diode forward charact., incl. $R_{CC'+EE'}$

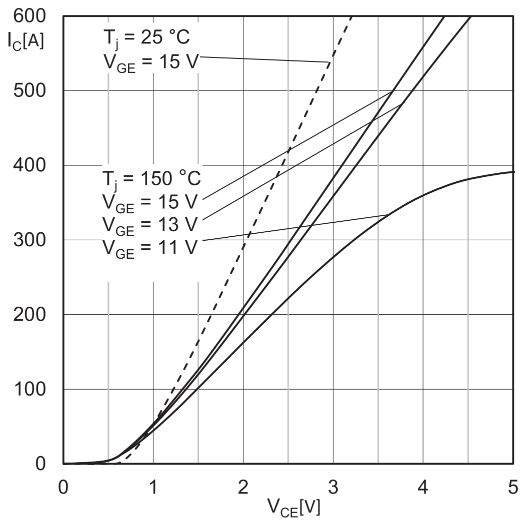


Fig. 13: Rated current vs. Temperature $I_{Shunt} = f(T_c)$

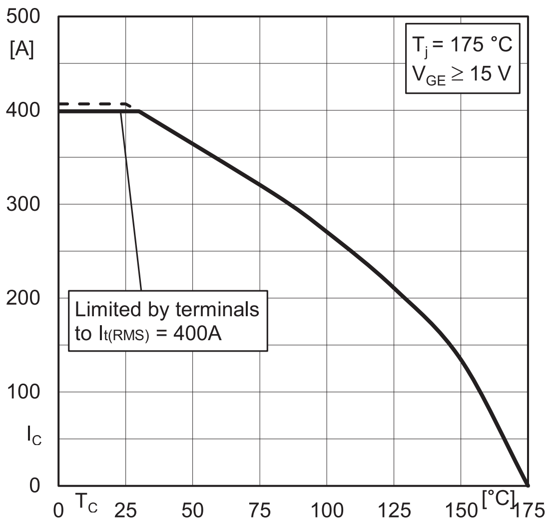


Fig. 14: Pulse current $I_{Shunt} = f(t_p)$

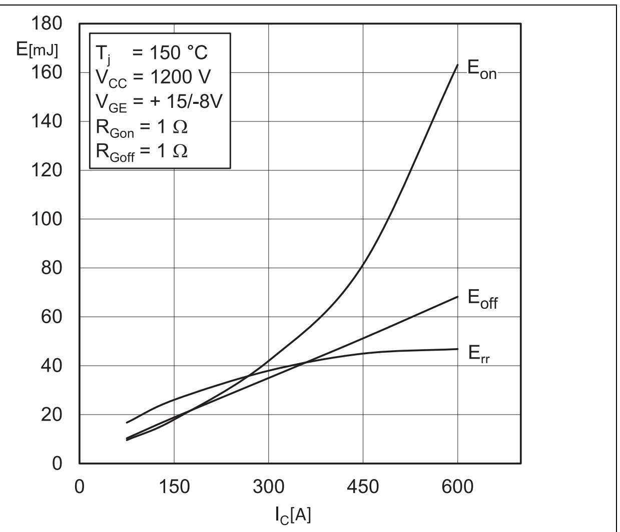


Fig. 15: Typ. IGBT2 & Diode1 turn-on /-off energy = f (I_C)

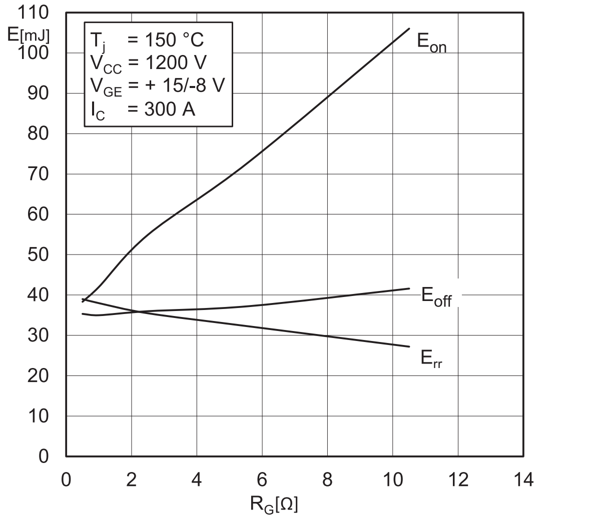


Fig. 16: Typ. IGBT2 & Diode1 turn-on / -off energy = f(R_G)

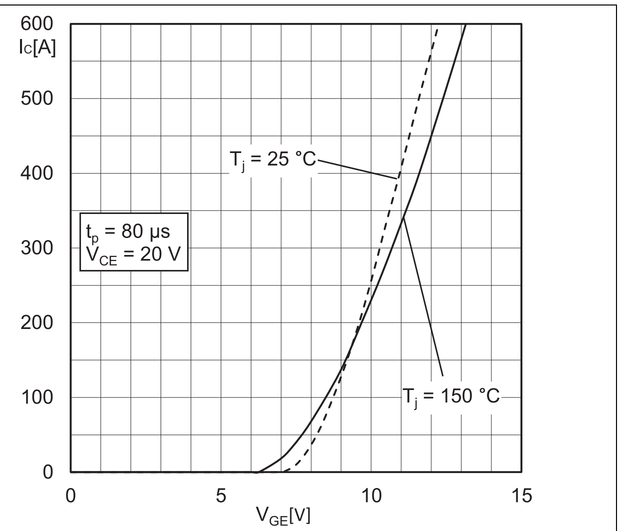


Fig. 17: Typ. IGBT2 transfer characteristic

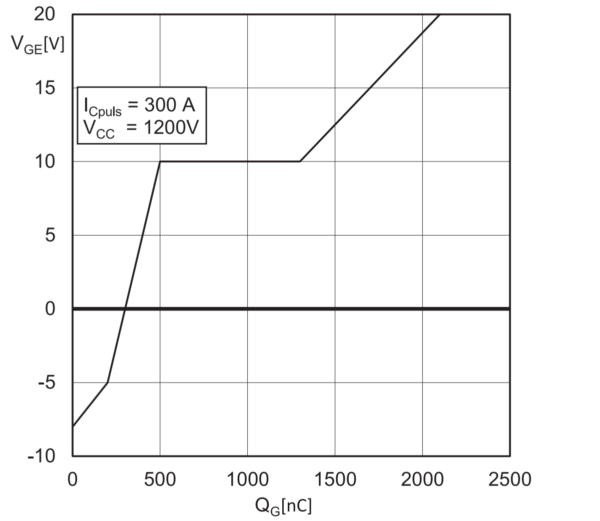


Fig. 18: Typ. IGBT2 gate charge characteristic

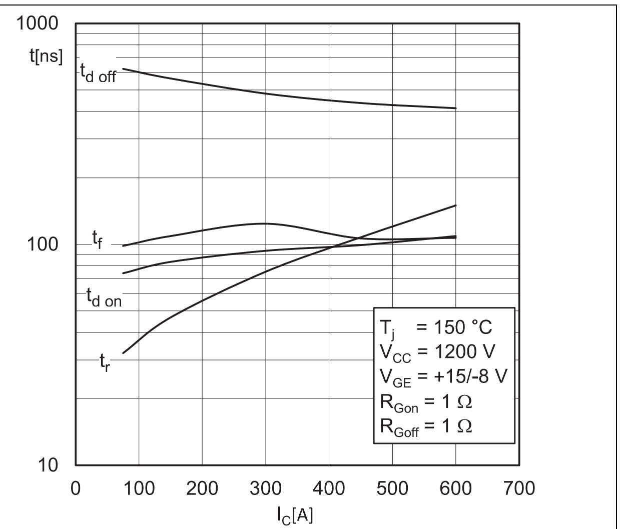


Fig. 19: Typ. IGBT2 switching times vs. I_C

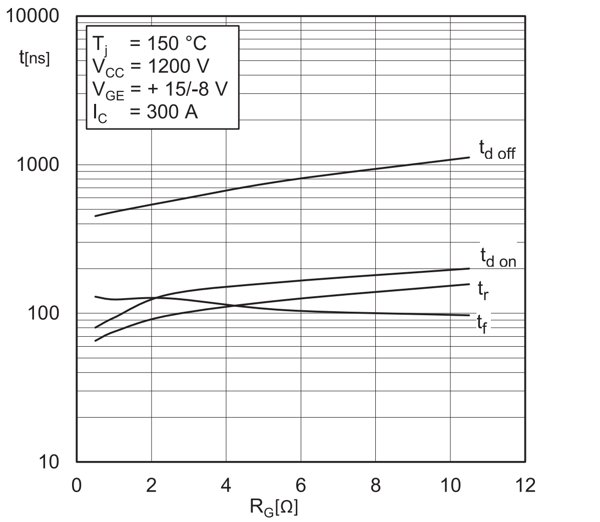


Fig. 20: Typ. IGBT2 switching times vs. gate resistor R_G

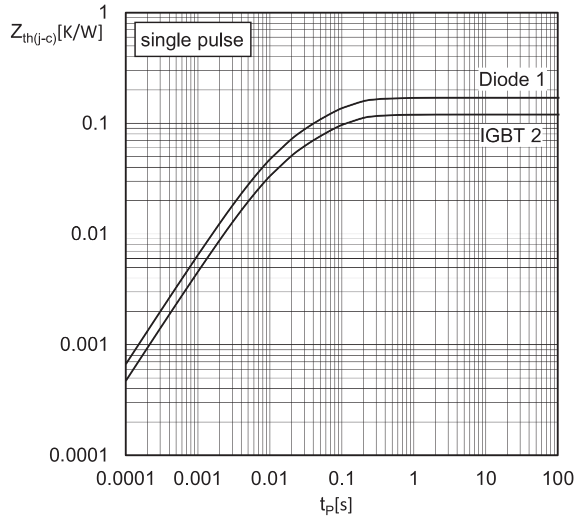


Fig. 21: Transient thermal impedance of IGBT2 & Diode1

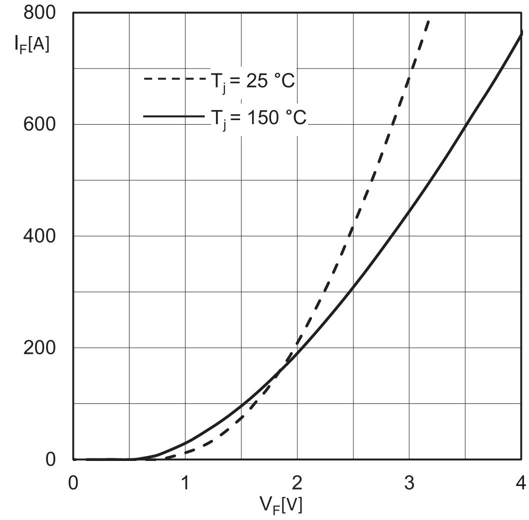
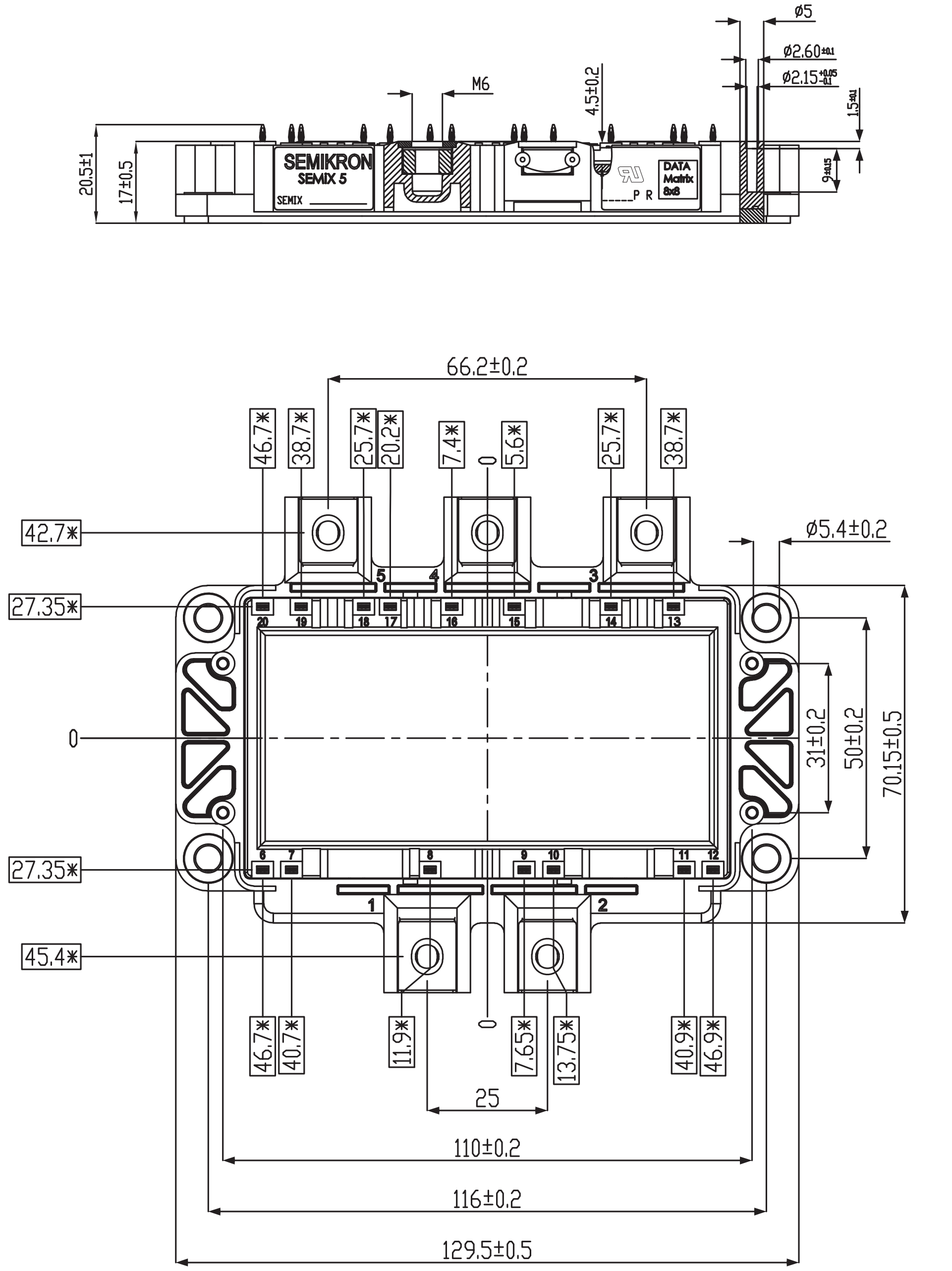


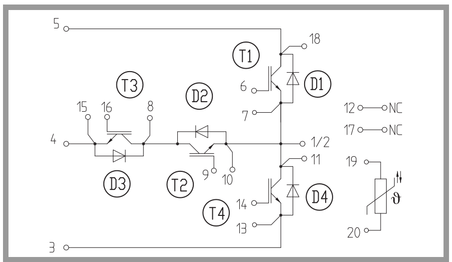
Fig. 22: Diode1 forward characteristic



* = Dimensions in mm with tolerance of ⌖ Ø 0.4

For technical details please refer to SEMiX(R)5 Mounting Instruction

SEMiX5p



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IMPORTANT INFORMATION AND WARNINGS

This is an electrostatic discharge sensitive device (ESDS) according to international standard IEC 61340.

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